

# Phase Control Thyristors (Hockey PUK Version), 910 A



**B-PUK (TO-200AC)** 

PRIMARY CHARACTERISTICS					
I <sub>T(AV)</sub>	910 A				
V <sub>DRM</sub> /V <sub>RRM</sub>	1200 V, 1600 V, 1800 V, 2000 V				
$V_{TM}$	1.80 V				
I <sub>GT</sub>	100 mA				
TJ	-40 °C to +125 °C				
Package	B-PUK (TO-200AC)				
Circuit configuration	Single SCR				

#### **FEATURES**

- · Center amplifying gate
- Metal case with ceramic insulator
- International standard case B-PUK (TO-200AC)



- Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>

#### **TYPICAL APPLICATIONS**

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	TEST CONDITIONS	VALUES	UNITS			
1		910	A			
I <sub>T(AV)</sub>	T <sub>hs</sub>	55	°C			
1		1857	A			
IT(RMS)	T <sub>hs</sub>	25	°C			
1	50 Hz	15 700	A			
I <sub>TSM</sub>	60 Hz	16 400	^			
<sup>2</sup> t	50 Hz	1232	kA <sup>2</sup> s			
	60 Hz	1125	KA-5			
V <sub>DRM</sub> /V <sub>RRM</sub>		1200 to 2000	V			
t <sub>q</sub>	Typical	150	μs			
T <sub>J</sub>		-40 to 125	°C			

VOLTAGE F	VOLTAGE RATINGS									
TYPE NUMBER	VOLTAGE CODE VDRM/VRRM, MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V		V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	$I_{DRM}/I_{RRM}$ MAXIMUM AT $T_J = T_J$ MAXIMUM mA						
	12	1200	1300							
VS-ST700CL 16		1600	1700	80						
V3-31700CL	18	1800	1900	00						
	20	2000	2100							



ABSOLUTE MAXIMUM RATINGS	<b>S</b>					
PARAMETER	SYMBOL		VALUES	UNITS		
Maximum average on-state current	L	180° condu	ction, half sine v	wave	910 (355)	Α
at heatsink temperature	$I_{T(AV)}$	double side	(single side) co	oled	55 (85)	°C
Maximum RMS on-state current	I <sub>T(RMS)</sub>	DC at 25 °C	heatsink tempe	erature double side cooled	1857	
		t = 10 ms	No voltage		15 700	
Maximum peak, one-cycle	<b>L</b>	t = 8.3 ms	reapplied	1	16 400	A kA <sup>2</sup> s
non-repetitive surge current	I <sub>TSM</sub>	t = 10 ms	100 % V <sub>RRM</sub>		13 200	
		t = 8.3 ms	reapplied	Sinusoidal half wave,	13 800	
Maximum I <sup>2</sup> t for fusing		t = 10 ms	No voltage reapplied	initial $T_J = T_J$ maximum	1232	
	l <sup>2</sup> t	t = 8.3 ms			1125	
Waximum Floriusing		t = 10 ms	100 % V <sub>RRM</sub>		871	
		t = 8.3 ms	reapplied		795	
Maximum $I^2\sqrt{t}$ for fusing	I <sup>2</sup> √t	t = 0.1 to 10	) ms, no voltage	e reapplied	12 321	kA²√s
Low level value of threshold voltage	V <sub>T(TO)1</sub>	(16.7 % x π	$x \ I_{T(AV)} < I < \pi \ x$	$I_{T(AV)}$ ), $T_J = T_J$ maximum	1.00	V
High level value of threshold voltage	$V_{T(TO)2}$	$(I > \pi \times I_{T(AV)})$	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			V
Low level value of on-state slope resistance	r <sub>t1</sub>	(16.7 % x $\pi$ x $I_{T(AV)}$ < I < $\pi$ x $I_{T(AV)}$ ), $T_J = T_J$ maximum			0.40	mΩ
High level value of on-state slope resistance	r <sub>t2</sub>	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			0.35	1115.2
Maximum on-state voltage	$V_{TM}$	$I_{pk} = 2000 \text{ A}, T_J = T_J \text{ maximum}, t_p = 10 \text{ ms sine pulse}$			1.80	V
Maximum holding current	l <sub>Η</sub>	T. = 25 °C	T OF °C anada sumply 10 V resistive land			mA
Typical latching current	ΙL	T <sub>J</sub> = 25 °C, anode supply 12 V resistive load			1000	IIIA

SWITCHING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 $\Omega$ , $t_r \le 1~\mu s$ $T_J = T_J$ maximum, anode voltage $\le 80~\%~V_{DRM}$	1000	A/μs		
Typical delay time	t <sub>d</sub>	Gate current 1 A, $dl_g/dt = 1 A/\mu s$ $V_d = 0.67 \% V_{DRM}, T_J = 25 °C$	1.0			
Typical turn-off time	t <sub>q</sub>	$I_{TM}$ = 750 A, $T_J$ = $T_J$ maximum, $dI/dt$ = 60 A/ $\mu$ s, $V_R$ = 50 V, $dV/dt$ = 20 V/ $\mu$ s, gate 0 V 100 $\Omega$ , $t_p$ = 500 $\mu$ s	150	μs		

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	T <sub>J</sub> = T <sub>J</sub> maximum linear to 80 % rated V <sub>DRM</sub>	500	V/µs
Maximum peak reverse and off-state leakage current	I <sub>RRM</sub> , I <sub>DRM</sub>	$T_J = T_J$ maximum, rated $V_{DRM}/V_{RRM}$ applied	80	mA



TRIGGERING						
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES		UNITS
FANAIVIETEN	STWIBOL	I Ex	31 CONDITIONS	Тур.	Max.	UNITS
Maximum peak gate power	P <sub>GM</sub>	$T_J = T_J$ maximum,	$t_p \leq 5 \; ms$	10.0		W
Maximum average gate power	P <sub>G(AV)</sub>	$T_J = T_J$ maximum,	f = 50  Hz, d% = 50	2	.0	"
Maximum peak positive gate current	I <sub>GM</sub>	$T_J = T_J$ maximum,	$t_p \leq 5 \ ms$	3	.0	Α
Maximum peak positive gate voltage	+V <sub>GM</sub>	T. – T. maximum	t < 5 mg	20		V
Maximum peak negative gate voltage	-V <sub>GM</sub>	$T_J = T_J$ maximum, $t_p \le 5$ ms			.0	]
	I <sub>GT</sub>	T <sub>J</sub> = -40 °C	Maximum required gate	200	-	
DC gate current required to trigger		T <sub>J</sub> = 25 °C		100	200	mA
		T <sub>J</sub> = 125 °C	trigger/	50	-	
		T <sub>J</sub> = -40 °C	current/voltage are the lowest value which will trigger all units	2.5	-	
DC gate voltage required to trigger	$V_{GT}$	T <sub>J</sub> = 25 °C	12 V anode to cathode applied	1.8	3.0	V
		T <sub>J</sub> = 125 °C		1.1	-	
DC gate current not to trigger	I <sub>GD</sub>	$T_J = T_J \ maximum \\ maximum gate current/voltage \\ not to trigger is the maximum \\ value \ which \ will \ not trigger \ any \\ unit \ with \ rated \ V_{DRM} \ anode \ to \\ cathode \ applied$		1	0	mA
DC gate voltage not to trigger	V <sub>GD</sub>			0.	25	V

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum operating junction temperature range	$T_J$		-40 to 125	°C	
Maximum storage temperature range	T <sub>Stg</sub>		-40 to 150	C	
Maximum thermal resistance, junction to heatsink	р	DC operation single side cooled	0.073		
maximum thermal resistance, junction to heatsink	R <sub>thJ-hs</sub>	DC operation double side cooled	0.031	K/W	
Maximum thermal resistance, case to heatsink	-	DC operation single side cooled	0.011	IV VV	
waximum thermal resistance, case to neatsink	R <sub>thC-hs</sub>	DC operation double side cooled	0.006		
Mounting force, ± 10 %			14 700 (1500)	N (kg)	
Approximate weight			255	g	
Case style		See dimensions - link at the end of datasheet	B-PUK (TO-	200AC)	

△R <sub>thJ-hs</sub> CONDUCTION							
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION		RECTANGULAR CONDUCTION		TEST COMPLETIONS	LIMITE	
CONDUCTION ANGLE	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE	TEST CONDITIONS	UNITS	
180°	0.009	0.009	0.006	0.006	$T_J = T_J$ maximum		
120°	0.011	0.011	0.011	0.011			
90°	0.014	0.014	0.015	0.015		K/W	
60°	0.020	0.020	0.021	0.021			
30°	0.036	0.036	0.036	0.036			

#### Note

• The table above shows the increment of thermal resistance R<sub>thJ-hs</sub> when devices operate at different conduction angles than DC



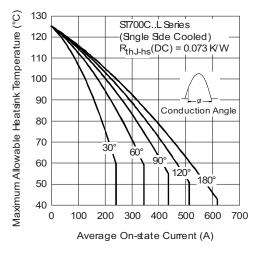


Fig. 1 - Current Ratings Characteristics

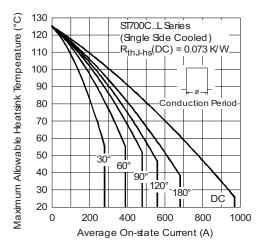


Fig. 2 - Current Ratings Characteristics

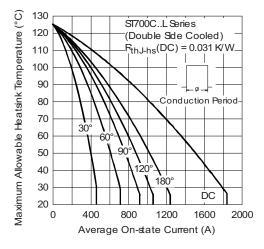


Fig. 3 - Current Ratings Characteristics

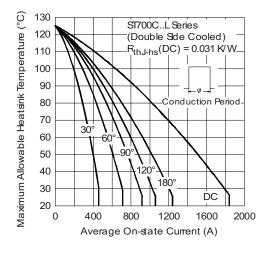


Fig. 4 - Current Ratings Characteristics

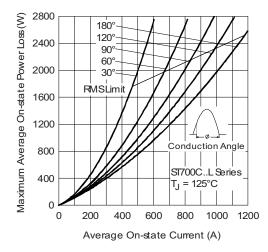


Fig. 5 - On-State Power Loss Characteristics

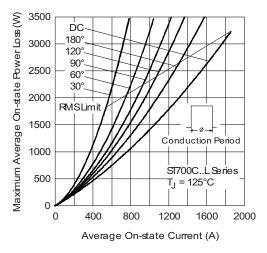


Fig. 6 - On-State Power Loss Characteristics

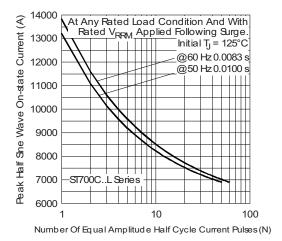


Fig. 7 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

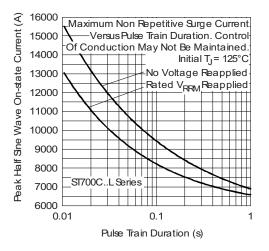


Fig. 8 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

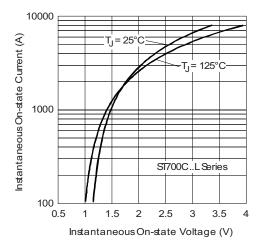


Fig. 9 - On-State Voltage Drop Characteristics

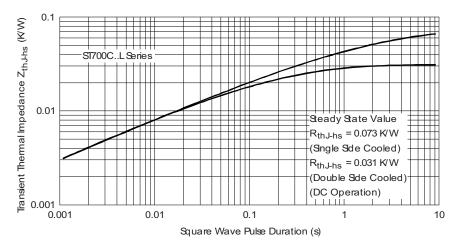


Fig. 10 - Thermal Impedance  $Z_{thJ\text{-}hs}$  Characteristics

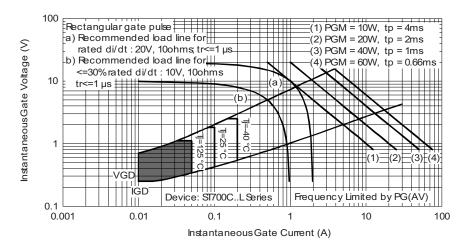
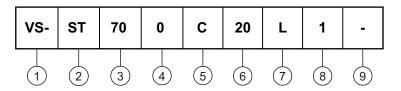


Fig. 11 - Gate Characteristics

#### **ORDERING INFORMATION TABLE**

**Device code** 



Vishay Semiconductors product

2 - Thyristor

Essential part number

4 - 0 = converter grade

5 - C = ceramic PUK

6 - Voltage code x 100 = V<sub>RRM</sub> (see Voltage Ratings table)

7 - L = PUK case B-PUK (TO-200AC)

8 - 0 = eyelet terminals (gate and auxiliary cathode unsoldered leads)

1 = fast-on terminals (gate and auxiliary cathode unsoldered leads)

2 = eyelet terminals (gate and auxiliary cathode soldered leads)

3 = fast-on terminals (gate and auxiliary cathode soldered leads)

9 - Critical dV/dt: • None = 500 V/μs (standard selection)

• L = 1000 V/µs (special selection)

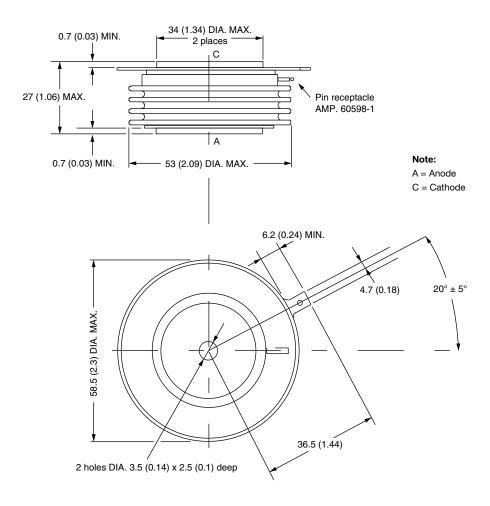
LINKS TO RELATED DOCUMENTS			
Dimensions	www.vishay.com/doc?95076		



# **B-PUK (TO-200AC)**

#### **DIMENSIONS** in millimeters (inches)

Creepage distance: 36.33 (1.430) minimum Strike distance: 17.43 (0.686) minimum



Quote between upper and lower pole pieces has to be considered after application of mounting force (see thermal and mechanical specification)



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